

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/BD/08A(10-01)
Approved for use through 10/21/2002. OMB 051-0001
This form is OMB U.S. DEPARTMENT OF COMMERCE
Patent Office unless it contains a valid OMB control number.

Sheet 1 of 1

Complete if Known

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Attorney Docket No: 1303.029US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
LP	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
LP	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T *
LP		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000), pp. 531-537	
LP		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000), pp. 105-113	
LP		FERGUSON, J D., et al., "Atomic layer deposition of Al ₂ O ₃ and SiO ₂ on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292	
LP		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta ₂ O ₅ films", <u>Journal of the Korean Physical Society</u> , (December 2000), pp. 975-979	
LP		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), 4 pages	
LP		KUKLI, KAUPU , "Atomic Layer Deposition of Titanium Oxide from TiI ₄ and H ₂ O ₂ ", <u>Chemical Vapor Deposition</u> , (2000), pp. 303-310	
LP		KUKLI, KAUPU , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272	
LP		KUKLI, KAUPU , et al., "Real-time monitoring in atomic layer deposition of TiO ₂ from TiI ₄ and H ₂ O-H ₂ O ₂ ", <u>American Chemical Society</u> , (2000), pp. 8122-8128	
LP		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al ₂ O ₃ Gate Dielectric", <u>IEDM</u> , (2000), pp. 645-648	
LP		PARANJPE, AJIT , et al., "Atomic layer deposition of AlO _x for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001), pp. 465-471	
LP		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 2 pages	

EXAMINER

DATE CONSIDERED

12/11/03

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Indicate reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached